TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC2655

Power Amplifier Applications Power Switching Applications

- Low saturation voltage: V_{CE} (sat) = 0.5 V (max) (IC = 1 A)
- High collector power dissipation: PC = 900 mW
- High-speed switching: $t_{stg} = 1.0 \mu s$ (typ.)
- Complementary to 2SA1020.

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	50	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	IC	2	Α	
Base current	ΙΒ	0.5	Α	
Collector power dissipation	PC	900	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

Unit: mm

Industrial Applications

	5.1 MAX.	
0.75MA)	8.2MAX.	
1.0MAX		
KAM8.0 KAM8.0		
<u>1</u>	27 1.27 1 2 3 X 2.54 WW 0 0 X X WW 1 4 W W	
1. EMITTE 2. COLLEG 3. BASE	:R	
JEDEC TO-92MOD		
JEITA	_	
TOSHIBA	2-5J1A	

Weight: 0.36 g (typ.)

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

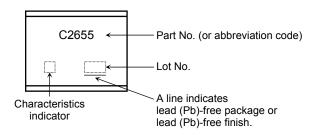


Electrical Characteristics (Ta = 25°C)

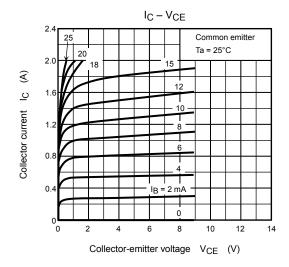
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I _{CBO}	V _{CB} = 50 V, I _E = 0	_	_	1.0	μΑ
Emitter cut-off cur	rrent	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	1.0	μΑ
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	50	_	_	V
DC current gain		h _{FE (1)} (Note)	V _{CE} = 2 V, I _C = 0.5 A	70	_	240	
		h _{FE (2)}	V _{CE} = 2 V, I _C = 1.5 A	40	_	_	
Collector-emitter	saturation voltage	V _{CE} (sat)	I _C = 1 A, I _B = 0.05 A	_	_	0.5	V
Base-emitter satu	ıration voltage	V _{BE} (sat)	I _C = 1 A, I _B = 0.05 A	_	_	1.2	V
Transition frequer	ncy	f _T	V _{CE} = 2 V, I _C = 0.5 A	_	100	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _C = 0, f = 1 MHz	_	30	_	pF
Switching time Storag	Turn-on time	t _{on}	20 μs Input B1 Output	_	0.1	_	
	Storage time	t _{stg}	20 μs Input IB1 Output Input IB1 Output Input IB2 Output CC OUTPUT CO OU	_	1.0	_	μs
	Fall time	t _f	30 V I _{B1} = -I _{B2} = 0.05 A, duty cycle ≤ 1%	_	0.1	_	

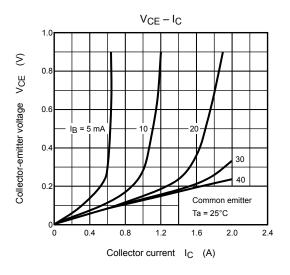
Note: h_{FE} (1) classification O: 70 to 140, Y: 120 to 240

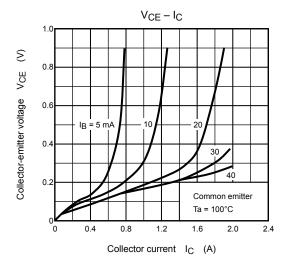
Marking

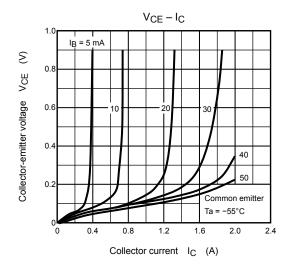


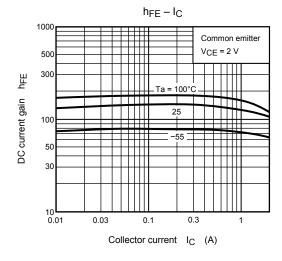
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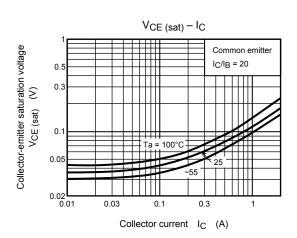


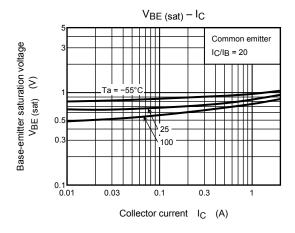


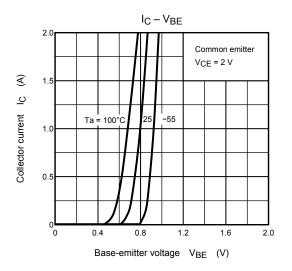


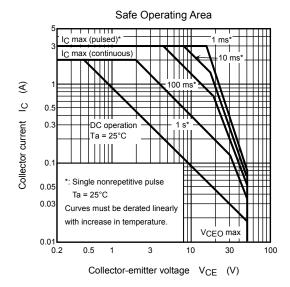


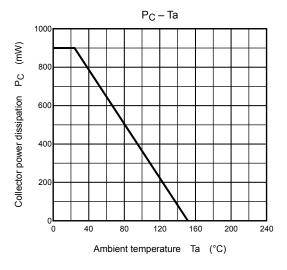












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